



Patent

7150-159P

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Hiroshi HAMADA et al. BATCH NO: E75

SERIAL NO: 07/340,777 GROUP: 254

FILED: April 20, 1989 EXAMINER: Mai

FOR: A LIQUID CRYSTAL ACTIVE-MATRIX DISPLAY DEVICE

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents
and Trademarks
Washington, D.C. 20231

July 16, 1990

Sir:

Pursuant to the duty of disclosure provisions pursuant to 37 CFR 1.56, the Applicants hereby submit a statement in accordance with 37 CFR 1.97-1.99.

REFERENCES

The Examiner is respectfully requested to give consideration to the documents listed on the PTO-1449 form attached hereto and to make these documents of record in the file wrapper of the present application. Initially, these documents were both to be submitted in an Information Disclosure Statement of April 20, 1989, in connection with the above-identified application. However, due to an inadvertent error, Japanese Laid-Open Patent Publication No. 62-66666 and an English language abstract thereof were submitted for consideration by the Examiner but not listed on the PTO-1449 form. Further, Japanese Laid-Open Patent Publication No. 62-10619 was listed on the PTO-1449, but a copy and an English language translation of the abstract thereof were not submitted

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in the Information Disclosure Statement of April 20, 1989. Therefore, the Examiner, in response to the Information Disclosure Statement of April 20, 1990, indicated consideration of Japanese Laid-Open Patent Publication No. 62-10619 and not Japanese Laid-Open Patent Publication No. 62-66666. Therefore, both Japanese Laid-Open Patent Publication No. 62-10619 and an English language translation of the abstract thereof and Japanese Laid-Open Patent Publication No. 62-66666 and an English language translation of the abstract thereof, are being submitted for consideration by the Examiner.

STATEMENT OF RELEVANCY

Japanese Laid Open Patent Publication No. 62-66666 is directed to an active matrix substrate. The active matrix substrate is disclosed in which a portion of the gate electrode of the thin film transistor, that is a polycrystalline silicon film with a thickness of 500 Å, overlaps the drain electrode of the thin film transistor through an insulating film. This thereby results in a capacitor.

Japanese Laid-Open Patent Publication No. 62-10619 is directed to an active matrix panel. The active matrix panel with a MOS capacitor is formed by the use of an insulating film with the same structure as that of the gate insulating film of the thin film transistor. The MOS capacitor is parallel to a capacitor provided by the liquid crystal cell formed in the panel. Further, one electrode of the MOS

capacitor is connected to each of the picture element electrodes and the other electrode is connected to a gate wiring for picture elements, or a line, at a fixed potential level that is adjacent thereto in the longitudinal direction.

This statement is not to be construed as a representation that a search has been made or that no better art exists.

Please charge any fees or credit any overpayment pursuant to 37 C.F.R. 1.16 or 1.17 to Deposit Account No. 02-2448.

Respectfully submitted,

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